100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET
POWERDI1012-8 (TOLL)

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
100V	2mΩ @ V_{GS} = 10V	250A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Wettable Flank for Improved Optical Inspection
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH10H1M7STLWQ)**

Description and Applications

This new generation N-Channel enhancement mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

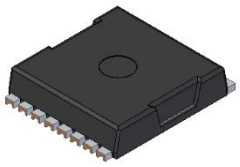
Applications

- Motor Control
- DC-DC Converters
- Power Management

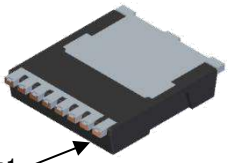
Mechanical Data

- Package: POWERDI1012-8 (TOLL)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.388 grams (Approximate)

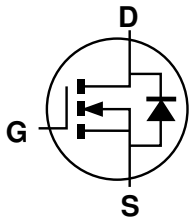
POWERDI1012-8



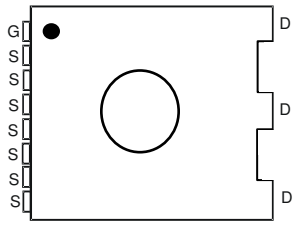
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

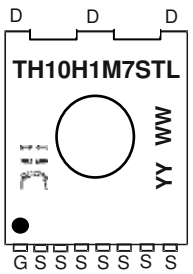
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH10H1M7STLW-13	POWERDI1012-8	1,500	Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI1012-8



= Manufacturer's Marking
TH10H1M7STL = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

POWERDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	250 176	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	1000	A
Maximum Continuous Body Diode Forward Current (Note 6)		I_S	250	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	1000	A
Avalanche Current, L = 0.3mH		I_{AS}	73	A
Avalanche Energy, L = 0.3mH		E_{AS}	799.4	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	6	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	24	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	250	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	0.6	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.4	2	mΩ	V_{GS} = 10V, I_D = 30A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 30A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	9871	—	pF	V_{DS} = 50V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	3019	—		
Reverse Transfer Capacitance	C_{rss}	—	58	—		
Gate Resistance	R_g	—	2.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	147	—	nC	V_{DD} = 50V, I_D = 30A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	43	—		
Gate-Drain Charge	Q_{gd}	—	32	—		
Turn-On Delay Time	$t_{D(ON)}$	—	29	—	ns	V_{DD} = 50V, V_{GS} = 10V, I_D = 30A, R_g = 4.7Ω
Turn-On Rise Time	t_R	—	64	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	108	—		
Turn-Off Fall Time	t_F	—	69	—		
Reverse Recovery Time	t_{RR}	—	91	—	ns	I_F = 25A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	270	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

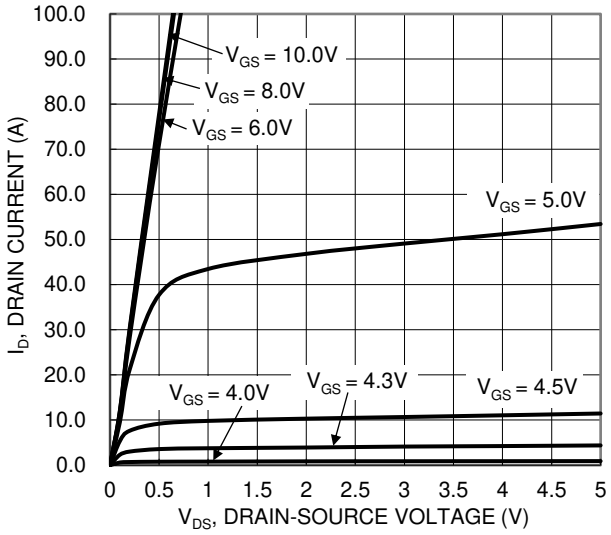


Figure 1. Typical Output Characteristic

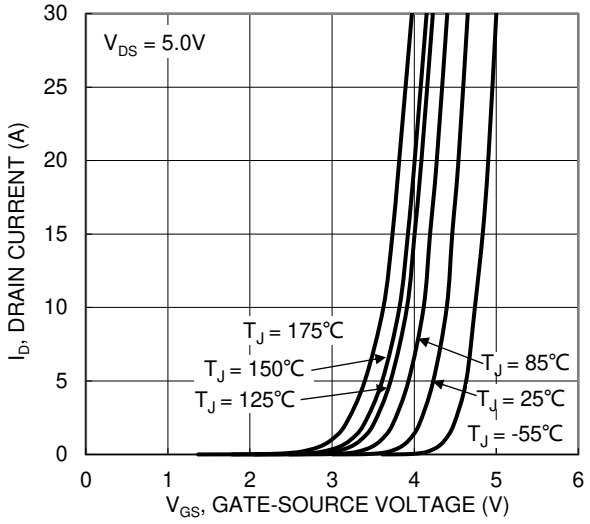


Figure 2. Typical Transfer Characteristic

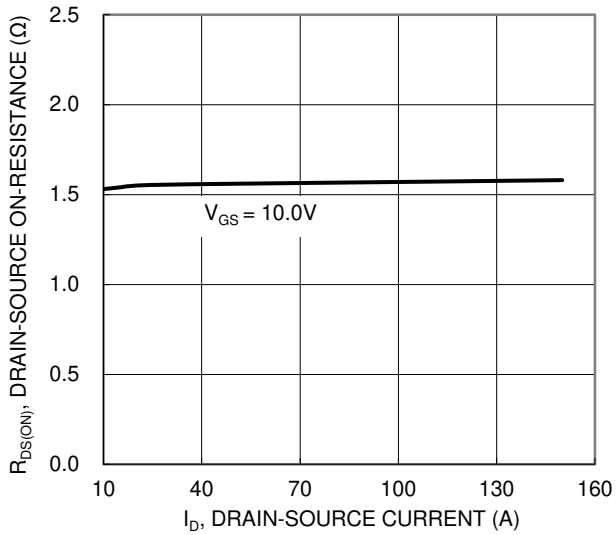


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

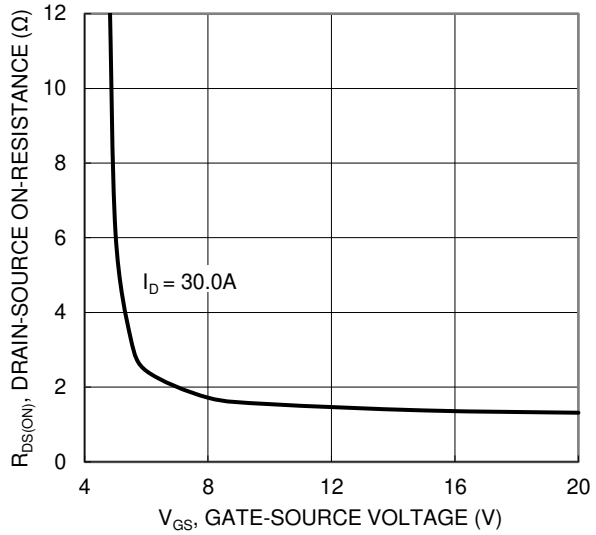


Figure 4. Typical Transfer Characteristic

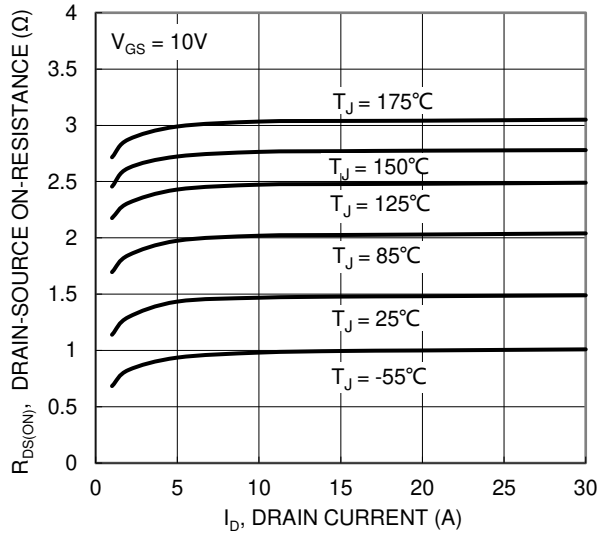


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

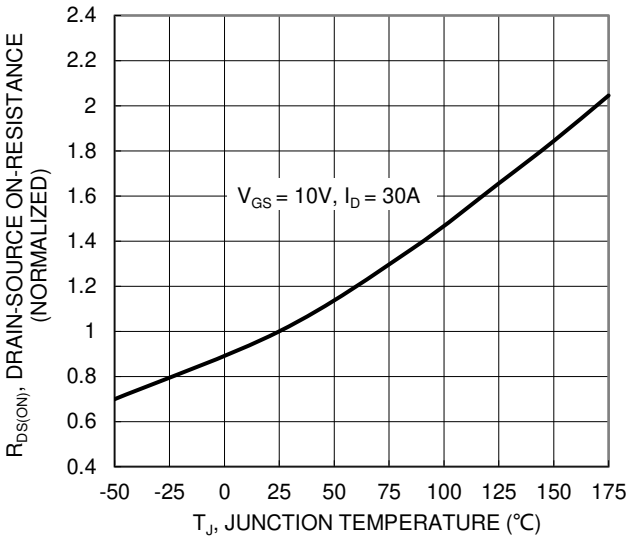


Figure 6. On-Resistance Variation with Temperature

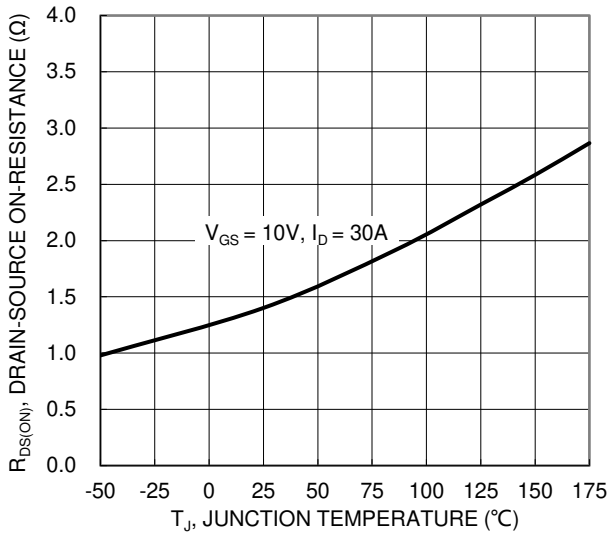


Figure 7. On-Resistance Variation with Temperature

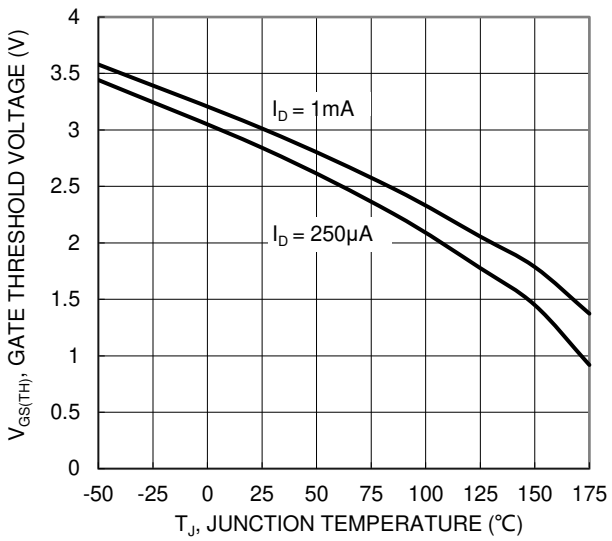


Figure 8. Gate Threshold Variation vs. Junction Temperature

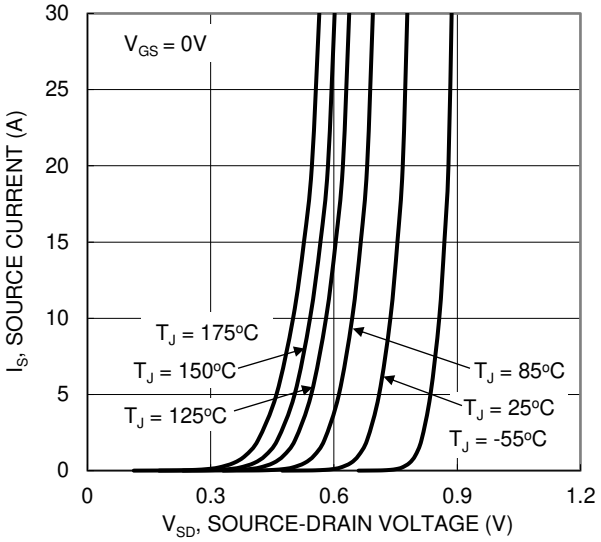


Figure 9. Diode Forward Voltage vs. Current

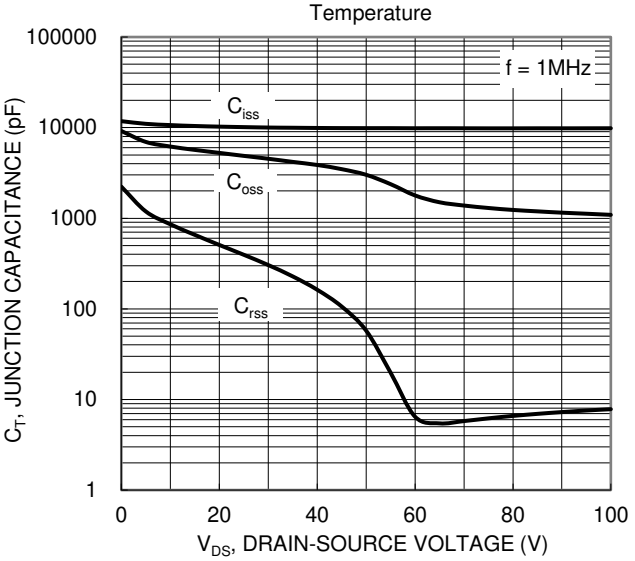


Figure 10. Typical Junction Capacitance

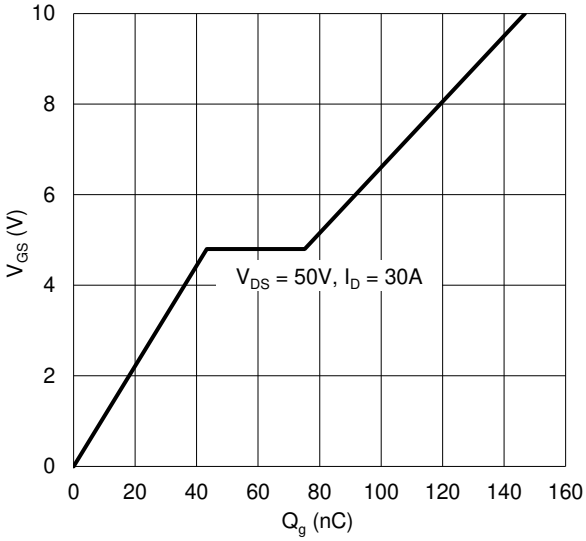


Figure 11. Gate Charge

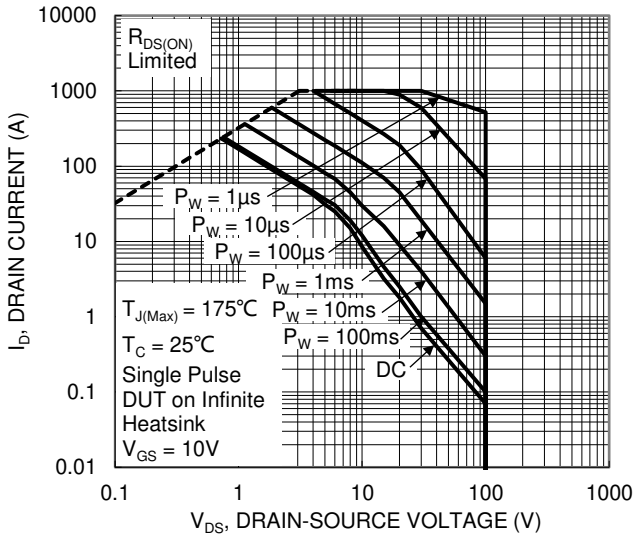


Figure 12. SOA, Safe Operation Area

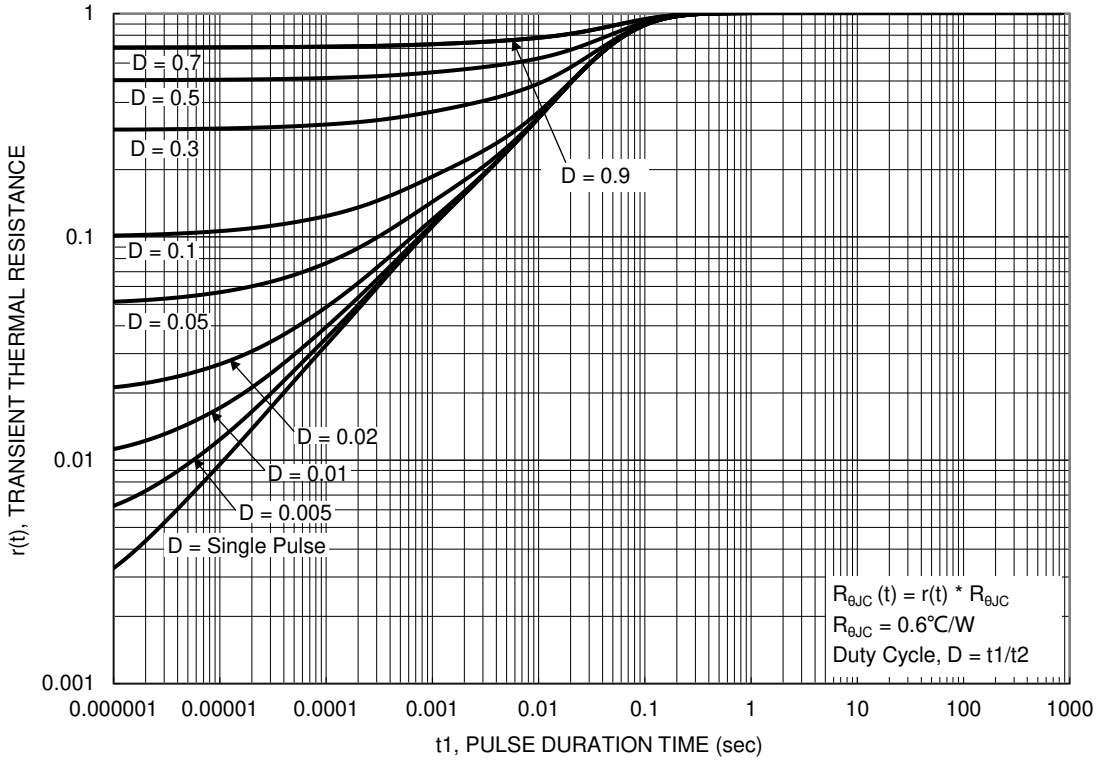
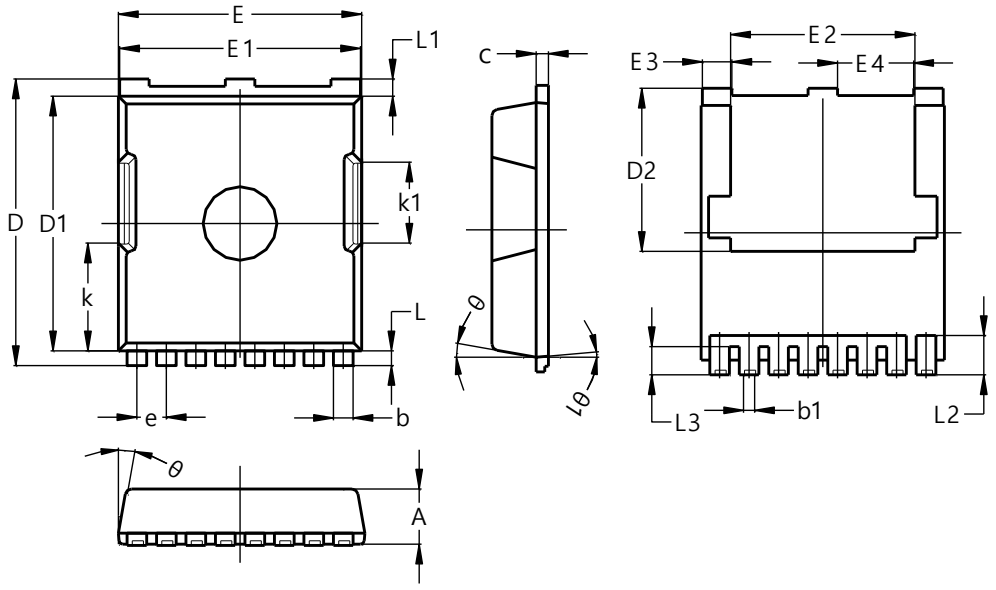


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

POWERDI1012-8

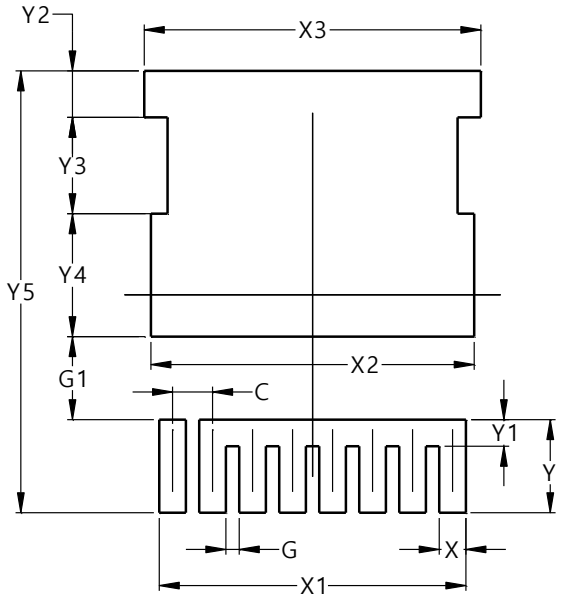


POWERDI1012-8			
Dim	**Min**	**Max**	**Typ**
A	2.20	2.40	2.30
b	0.70	0.90	0.80
b1	0.42	0.50	0.45
c	0.40	0.60	0.50
D	11.48	11.88	11.68
D1	10.23	10.53	10.38
D2	6.45	6.85	6.65
E	9.70	10.10	9.90
E1	9.70	9.90	9.80
E2	7.00	8.00	7.50
E3	1.10	1.30	1.20
E4	3.00	3.20	3.10
e	1.20 BSC		
k	4.39 REF		
k1	3.30 REF		
L	0.50	0.70	0.60
L1	0.50	0.90	0.70
L2	1.40	1.80	1.60
L3	1.00	1.30	1.15
θ	0º	15º	10º
θ1	0º	10º	5º
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

POWERDI1012-8



Dimensions	Value (in mm)
C	1.200
G	0.400
G1	2.500
X	0.800
X1	9.200
X2	9.700
X3	10.100
Y	2.800
Y1	0.800
Y2	1.400
Y3	2.900
Y4	3.700
Y5	13.300

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